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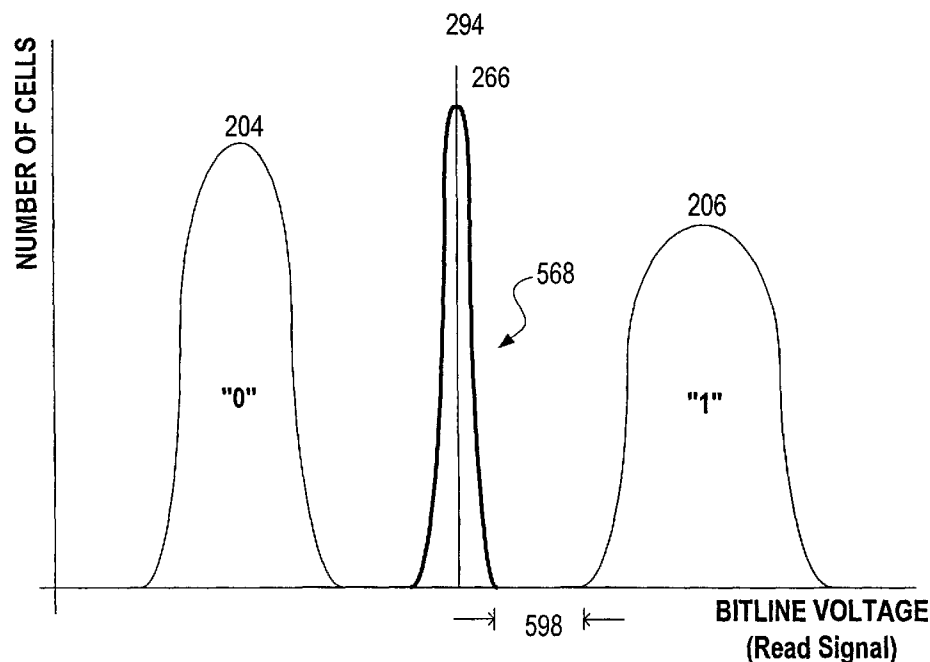
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(54) Title: REFERENCE VOLTAGE GENERATION FOR MEMORY CIRCUITS



(57) Abstract: An improved reference voltage generation is described. In one embodiment, a memory block includes a plurality of memory cells interconnected by wordlines and bitlines. A plurality of reference cells are provided. A bitline includes a reference cell. The bitlines of the memory block are divided into groups or bitlines. Only the reference cells within a group are interconnected to average out the reference cell charge variation to improve the sensing window.

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